## Correlation Induced Insulator to M etal Transitions

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W e study a spinless two-band m odel at half-lling in the limit of in nite dimensions. The ground state of this model in the non-interacting limit is a band-insulator. W e identify transitions to a metal and to a charge-M ott insulator, using a combination of analytical, Q uantum M onte C arlo, and zero temperature recursion methods. The metallic phase is a non-Ferm i liquid state with algebraic local correlation functions with universal exponents over a range of parameters.

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Strong correlations can lead to be energy behavior qualitatively di erent from that predicted by band theory. A classic example is provided by the M ott transition where a system, which is expected to be a band m etal, turns into an insulator as correlations become greater than a critical value. [1] R ecently, the complementary question of whether interactions can drive a band insulator into a m etal has been raised in connection with the possible (sem i)-m etallic nature of the \K ondo insulators". [2] From a theoretical point of view, it is likely that a m etal which exists only as the result of interactions can not be analytically continued to a free electron m etallic system and hence should not be described by Ferm i liquid theory. The related question of the possible existence of non-Ferm i liquid m etallic states has been of great recent interest, due to the anom alous norm al state properties of the high-T<sub>c</sub> oxides [3,4].

In this letter, we study a spinless model at half- lling which displays a band insulating ground state in the absence of interactions. We developed two numerical algorithms to study the the elects of interactions in in nite dimensions, supplementing the numerical results with analytical arguments. We not that, in spite of the simplicity of the model, the interactions give rise to a novel correlation-induced insulator (to which we refer as a charge-M ott insulator), and a non-Ferm i liquid metallic phase with scale invariant low-energy correlation functions. In the latter, we identify two parameter regimes, in which the associated exponents are continuously varying and universal, respectively.

W e study the follow ing H am iltonian

$$H = \begin{pmatrix} X \\ k \end{pmatrix} c_{k}^{y} c_{k} + \begin{pmatrix} X \\ d \end{pmatrix} (c_{i}^{y} c_{i} + h c_{i}) c_{i}^{y} d_{i} + \begin{pmatrix} X \\ d \end{pmatrix} (c_{i}^{y} c_{i} + h c_{i}) + \begin{pmatrix} X \\ d \end{pmatrix} (c_{i}^{y} c_{i} - \frac{1}{2}) (c_{i}^{y} d_{i} - \frac{1}{2});$$
(1)

where  $c^{v}$  and  $d^{v}$  are creation operators for two species of spinless electrons. The c-electrons have a dispersion <sub>k</sub>, while the d-band is dispersionless with local energy  $_{d}^{o}$ . These two species are coupled through the hybridization, t, and the density-density interaction, V. Below we focus on the half-lied case, with  $_{d}^{o} = _{c} = = 0$ .

We solve this model in the lim it of in nite dimensions [5] in which the hopping matrix

element  $t_{ij}$  must be rescaled with 1 = d. The one-particle G reen's function, G (k; i!<sub>n</sub>)

<sup>R</sup> d  $e^{i!_n}$  < T (k; ) <sup>y</sup> (k; ) >, with <sup>y</sup> = (d<sup>y</sup>; c<sup>y</sup>), can be calculated from the D yson's equation

$$G^{1}(k;i!_{n}) = \begin{bmatrix} 0 & 1 \\ B & i!_{n} + & a \\ C & t & E \\ t & i!_{n} + & k \end{bmatrix}$$
(2)

The self-energy (i!<sub>n</sub>) is momentum independent and can thus be calculated from the local G reen function,  $\langle y \rangle_{S_{imp}}$ , associated with the impurity action [6],

$$S_{imp}(G_{o}) = \int_{0}^{Z} d d^{0} ()G_{o}^{1}() ()G_{o}^{1}() () + \int_{0}^{Z} d V (d^{v}c - \frac{1}{2})(d^{v}d - \frac{1}{2})$$
(3)

according to the Dyson equation,  $= G_0^{1} < Y >_{S_{imp}}$ , where  $G_0$  obeys the selfconsistency equation  $P_k^{P} G(k; i!_n) = N_{site} = < Y >_{S_{imp}}$ . As is already implicit in the choice of the local action (3), we will focus on states with no long range (CDW) order [7].

The e ective-in purity action (3) can be equivalently written in terms of a resonant-level model,

$$H_{inp} = H_{o} + t(c^{y}d + d^{y}c) + ({}^{o}_{d} )d^{y}d + V(n_{d} \frac{1}{2})(n_{c} \frac{1}{2})$$
(4)

where  $H_{\circ}$  describes the local c-electron coupled to a non-interacting electron bath with a hopping matrix determined from the self-consistency equation. For simplicity we study the case of a semi-circular conduction-electron density of states,  $_{\circ}() = {}^{P}_{k} (_{k})=N_{site} = (2 = D)^{q} \overline{1 (=D)^{p}}$ , for which the self-consistency equation reduces to the form :

$$(G_{o}^{1})_{cc} = i!_{n} + (\frac{D}{2})^{2}G_{cc}$$
 (5)

We developed two numerical techniques to analyze Eqs. (3-5). The rst algorithm is a generalization of the method used in previous studies of the Hubbard model. [8{10] An initial guess for  $G_o$  is used in the impurity action Eq. (3), which is solved by M onte C arb method. Our algorithm is based on a modi cation of that due to H irsch and Fye [11], and uses a di erent set of Hubbard-Stratonovich variables [12] and a single determ inant. The calculated G reen's function is then fed into the self-consistency condition (5) and the procedure is iterated until convergence is achieved.

The second algorithm is based on the recursion method. [13,14] The one particle G reen's function can be written as  $G(z) = G^{>}(z) + G^{<}(z)$  where  $G^{>}(z) = {}^{R}d$  ()=(z) and

( ) = 0 for  $^{>}_{<}$  0. W e use the continued-fraction expression for G  $^{>}$  (z),

$$G^{>}(z) = \frac{b_{1}^{r}}{z \ a_{1}^{r}} \frac{b_{2}^{r}}{z \ a_{2}^{r}} ; \qquad (6)$$

and a similar one for  $G^{<}(z)$ , with  $a_i^r$  and  $b_i^r$  replaced by  $a_i^l$  and  $b_i^l$ . This representation obeys the correct analyticity requirements ( $b_1^r + b_1^l = 1$ ). It allows us to visualize the self-consistency equation, ( $G_0^{-1})_{cc} = i!_n$  ( $_c$ ) ( $D = 2)^2 G_{cc}$ , as the inverse of the local G reen's function  $< c^y c >$  of the non-interacting H am iltonian,

where N is the level of the continued-fraction expression which is in nite in the exact representation but taken as nite in practice. The problem can now be reformulated in terms of the self-consistent determ ination of the variables  $a_i^r$ ,  $a_i^l$ ,  $b_i^r$ , and  $b_i^l$  [15]. We start with an initial guess for these parameters, and solve the ground state j > of the resonant-level H am iltonian given by (4) and (7) using the standard sparse matrix diagonalization methods. [14] The new parameters  $a_i^r$ ,  $a_i^l$ ,  $b_i^r$ , and  $b_i^l$  for the next iteration is then obtained from the matrix elements of an orthogonal basis which tridiagonalizes  $H_{inp}$ . Speci cally,  $a_n^r = \langle f_n^r H_{inp} f_n^r \rangle = \langle f_n^r f_n^r \rangle$ , and  $b_n^r = \langle f_n^r f_n^r \rangle$  and for n 2,  $f_{n+1}^r \rangle = H_{inp} f_n^r \rangle$ ,  $a_n^r f_n^r \rangle = c^y j$ ,  $f_n^r r \rangle$ . Sim ilar equations, with  $f_1^1 \rangle = c^y j$ , give rise to  $a_i^l$  and  $b_i^l$ . Compared to the nite temperature M onte C arbom ethod, this algorithm works directly at zero temperature, and is less expansive numerically.

Using both methods, we nd that the model displays two kinds of insulating phases separated by a metallic phase. The phase diagram in the V t parameter space is shown schematically in Fig. 1. To illustrate the phase diagram, we plot in Fig. 2 the d-electron local G reen's function,  $G_{dd}$ , as a function of the M atsubara frequency for two parameters with a same value of the hybridization, t = 0.4D, and dierent values of the interaction, V = 0.1D and V = 2.5D, respectively. They clearly display the gap in their respective single particle excitation spectrum, and also demonstrate the excellent agreement between the zero temperature results from the recursion method and the low (but nite) temperature results from the Quantum M onte C arb. Shown in Fig. 3 are  $G_{dd}$ , as well as the c-electron local G reen's function,  $G_{cc}$ , for the hybridization identical to that used in Fig. 2, t = 0.4D, and an interaction strength in between those used in Fig. 2, V = 0.9D. The single-particle excitation spectrum is gapless in this case.

In order to clarify the nature of the phases and the structure of the phase diagram, we now consider various limiting cases where analytical arguments can be made. In the non-interacting limit (V = 0) = 0 and the G reen function (2) displays two branches of poles,  $E_k = (k^q - (k^q)^2 + 4t^2) = 2$ , describing the fully occupied bonding band () and the empty anti-bonding band (+). Thus, a hybridization gap  $_{o} = p - \frac{p}{D^2 + 4t^2}$  D, develops, leading to band-insulating behavior. This state becomes unstable whenever the elect of interactions is strong enough to close the hybridization gap.

This can be most easily seen in the atom ic  $\lim it, D = 0$ , in which case the behavior of the e ective in purity model (3-5) is determined by the local empty, doubly occupied, bonding and anti-bonding singly occupied electron states, respectively,

$$\begin{split}
\mathbf{E} &>= \mathbf{N} = \mathbf{0} >= \mathbf{j} > \\
\mathbf{p} &>= \mathbf{N} = 2 >= d^{\mathbf{y}} c^{\mathbf{y}} \mathbf{j} > \\
\mathbf{B} &>= \mathbf{N} = 1; \mathbf{b} >= \frac{1}{\mathbf{p} \cdot \frac{1}{2}} (d^{\mathbf{y}} - c^{\mathbf{y}}) \mathbf{j} > \\
\mathbf{A} &>= \mathbf{N} = 1; \mathbf{a} \mathbf{b} >= \frac{1}{\mathbf{p} \cdot \frac{1}{2}} (d^{\mathbf{y}} + c^{\mathbf{y}}) \mathbf{j} >;
\end{split}$$
(8)

The corresponding eigenvalues are (E) = (D) = V=4, (B) = V=4 t, and (A) = V=4

V=4 + t. Three parameter regimes occur in this limit: (i) For V < 2t the local bonding state,  $\beta$  >, has the lowest energy, and is separated by a mite gap from lowest single particle excitation, leading to band-insulating behavior; (ii) At V = 2t three states,  $\beta$  >, j >, and  $\pm$  >, become degenerate and metallic behavior with gapless single-particle excitations sets in; (iii) Finally, for V > 2t the low-energy charge doublet, j > and  $\pm$  >, is separated by a gap from the lowest single-particle excitation leading to a situation analogous to the M ott insulator of the atom ic limit of the half- lled repulsive H ubbard model, in which case the spin doublet is the lowest energy state. [9] W e thus refer to the resulting phase as a charge-M ott insulator. [16]

The stability of these three phases and the position of the boundaries between them, can also be understood analytically in the lim it of sm all hybridization. In that case, the instability of the band insulator, which occurs through the closing of the hybridization gap, is most easily seen in terms of the irrelevance of the hybridization coupling (in the sense of the renormalization group) for a su ciently large value of the attractive interaction, V. The value of the critical coupling,  $V_{c1}$ , follows from a scaling analysis of the resonant-level model (4), in the vicinity of the phase boundary from the metallic (t 0) side. It is obtained from the condition, t = 1, on the the anom alous dimension of the hybridization operator, t, de ned from the long time behavior of the auto-correlation function, () = <  $T d^{y}$  ()c() $\xi(0)d(0)$  >  $2^{t}$ . Such a condition implies [17] ( $V_{c1}$ ) $V_{c1}$  = (2=)tan [(2 - 1)=2]. Here, (V) = (2= D)= $\frac{q}{1}$  (V=D)<sup>2</sup> is the bath density of states at the Ferm i level which is itself dependent on V as a result of the self-consistency requirement (5). [18] This argument leads to  $V_{c1} = 0.6D$ . Upon further increasing the attraction beyond  $V_{c1}$  the charge-M ott gap develops at a second critical value,  $V_{c2}$ . The latter can be calculated from the exact solution of the Falicov-K in ballm odel (at d = 1) [19] corresponding to the Hamiltonian (1) with t = 0, and is identiced as the value of V at which the local conduction electron density of states at the Fermi energy,  $_{c}(0)$ , starts to vanish. For the sem i-circular density of states,  $_{c}(0) = (2 = D)^{4} \frac{1}{1 (\frac{V}{D})^{2}}$ ; [20] leading to  $V_{c2} = D$ . O ur num erical results are consistent with the analytical estim ates for  $V_{\rm cl}$  and  $V_{\rm c2}$  .

To further characterize the nature of the m etallic phase, we have analyzed numerically the low frequency behavior of the local G reen's functions. Consider nst the limit of small hybridizations. In this regime, we nd that  $G_d$  ij! n j sgn! n. This self-similar behavior is consistent with the irrelevant hybridization, which in plies a zero renormalized Ferm ienergy. [17] In this case, the exponent is expected to to be given by the orthogonality exponent,  $(-)^2$ , with the phase shift determined from the standard formula, =  $(2 = )\tan^1((V)V=2)$ . The numerically determined exponents are consistent with this analytical expression. Finally, the calculated c-electron local G reen's function, G<sub>∞</sub>, is nonsingular, as expected from a picture of the m etallic state in which the local degrees of freedom asymptotically decouple from the conduction-electron bath at low energies. [17,21]

The most interesting regin e of the metallic phase occurs for intermediate to large values of the hybridization (as well as the interaction strength). In this regine, our numerical results show that,  $G_{dd}$  continues to have a self-similar behavior, with an exponent close to 1, independent of the interaction strength. At the same time,  $G_{cc}$  is again nonsingular, suggesting that, even in the intermediate to large hybridization limit (for nite bandwidth, 2D), a partial decoupling of the d and c electron degrees of freedom occurs at low energies.

Such a partial decoupling of the local degrees of freedom, and the interactionindependence of the exponents, can be understood as a result of the self-consistent modication of the electron bath for the electric in purity model using the atom ic limit metallic state as a starting point. In that case, projecting onto the three degenerate low – energy atom ic states,  $\beta >$ , p >, and  $\pm >$ , in (8), leads to the representation of local fermions,  $c^{y} = \frac{1}{2} (X_{BE} + X_{DE})$  and  $d^{y} = \frac{1}{2} (X_{BE} - X_{DE})$  in terms of projection operators, X = j > < j. The corresponding low-energy spectral functions take the form,  $_{c}(!) = _{d}(!) = \frac{2}{3}$  (!). In the presence of the hopping term D, these atom ic con gurations are coupled to the self-consistent electron bath through the H<sub>o</sub> term in (4) which we parametrize as,  $H_{o} = \frac{P}{_{k}} V_{k} (c^{y}_{k} + H c;) + \frac{P}{_{k}} \chi_{k} \frac{y}{k}$ . The parameters,  $\gamma_{k}$  and  $V_{k}$ , are determ ined from the self-consistency condition,  $(1=N_{site})^{P} _{k} V_{k}^{2}$  ( $_{k}$ ) =  $(D=2)^{2} _{c}$ (), which corresponds to taking the in aginary part of Eq. (5). The form of  $_{c}$  in the atom ic limit

in plies that the electron bath k corresponds to a single level, created by  $y_{0}^{y}$ , at zero energy. Hence, the impurity problem reduces to  $\hat{H}_{imp} = \frac{B}{2^{p} - 3} [(X_{BE} + X_{DB})_{o} + hx:]$ , which acts on a Hilbert space spanned by  $\Xi >$ , B >, D > and  ${}^{y}_{\circ}E >$ ,  ${}^{y}_{\circ}B >$ ,  ${}^{y}_{\circ}D >$ . It is easily seen that the ground state manifold of this Ham iltonian is doubly degenerate and consists of the states  $\mathfrak{N} = 1 > = (1 = 2)(\mathfrak{B} > + \sqrt[9]{\mathfrak{E}} >)$ , and  $\mathfrak{N} = 2 > = (1 = 2)(\mathfrak{D} > + \sqrt[9]{\mathfrak{B}} >)$ . Recalculating the G reen functions of local ferm ions we obtain a zero energy pole in G  $_{\rm dd}$  and pairs of non-zero energy poles, symmetrically centered around zero, in G  $_{\rm cc}.$  This form of  $G_{\infty}$  then in plies that the electron bath for the next iteration is composed of pairs of levels i. It can be shown, following the same procedure, that for each pair of levels at energies coupled to the local c-electron, there again exist degenerate ground states, at energies leading to a zero energy pole in G  $_{dd}$  and pairs of non-zero energy poles in G  $_{\rm cc}.$  As the iteration proceeds, the poles in G  $_{\rm cc}$  spread over a range of the order of the bare bandwidth while a zero-energy pole persists in G<sub>dd</sub>, leading to the self-consistent solution with a regular  $G_{cc}$  and a self-sim ilar  $G_{dd}$  with the exponent = 1.

In sum mary, we reported a) novel transitions from a band-insulator to a metal and to a charge-M ott insulator within a simple spinless two-band model; and b) a novel non-Ferm i liquid metallic regime characterized by an algebraic local correlation functions with universal exponents. These local correlation functions are shown to be associated with a non-trivial elective in purity problem. And the very existence of this new non-Ferm i liquid is closely related to a level-crossing in the atom ic lim it of the associated in purity problem, a benchm ark for a class of non-Ferm i liquid states in a variety of strongly correlated in purity models [22,23,17,24]. Related ideas have been proposed in a phenom enological discussion of strongly correlated lattice models in which non-Ferm i liquid behavior arises due to the coexistence of single particle states and dispersionless three-body resonances at the chem ical potential. [25] The results of this letter are expected to have in portant in plications for models describing realistic strongly correlated system s such as the \K ondo-Insulators" and high T<sub>c</sub> copper oxides. In this regard we note that, while the metallic phase in our model occurs in a range of attractive interactions, these interactions should be understood as

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e ective parameters derived from the bare interactions in a more complex set of local orbitals in realmaterials. [26] W e also note that, in the spinful cases and away from half-lling, there can exist an intermediate non-Fermiliquid metallic state with coherent spin excitations and incoherent charge excitations. [17] O ur results here should describe the charge sector of the intermediate phase. These and other related questions are currently under investigation within more realistic models.

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## FIGURES

FIG.1. The qualitative phase diagram . Here BI'', M'', and CMI'' correspond to the band insulating, m etallic, and charge M ott insulating phases respectively.

FIG.2.  $G_{dd}$  vs. M atsubara frequency  $!_n$  for V = 0.1D and t = 0.4D (band insulator) calculated from the recursion m ethod (solid line) using 10 sites to truncate the impurity H am iltonian and 100 levels for the continued-fraction expansion, and from quantum M onte C arlo (circles) with = 32. Sim ilar results are shown (dashed line and squares) for V = 2.5D and t = 0.4D (charge-M ott insulator).

FIG.3.  $G_{dd}$  vs. M atsubara frequency  $!_n$  for V = 0.9D and t = 0.4D (m et al) calculated from the recursion m ethod (solid line) with 10 sites and 100 levels and quantum M onte C arlo (circles) with = 64. Inset plots the sim ilar results for  $G_{\infty}$ .